



SPP1027

Dual P-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPP1027 is the Dual P-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

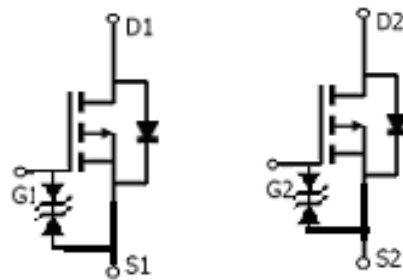
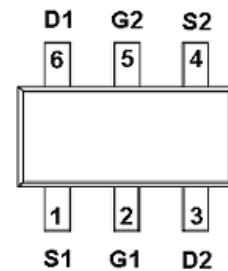
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

FEATURES

- ◆ P-Channel
 - 30V/0.45A, $R_{DS(ON)} = 0.65\Omega @ V_{GS} = -4.5V$
 - 30V/0.35A, $R_{DS(ON)} = 0.90\Omega @ V_{GS} = -2.5V$
 - 30V/0.25A, $R_{DS(ON)} = 1.50\Omega @ V_{GS} = -1.8V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-563 (SC-89-6L) package design

PIN CONFIGURATION(SOT-563 / SC-89-6L)



PART MARKING





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PIN DESCRIPTION

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	D2	Drain 2
4	S2	Source 2
5	G2	Gate 2
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP1027S56RGB	SOT-563	27

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)

※ SPP1027S56RGB : Tape Reel ; Pb – Free ; Halogen – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	-0.45
		TA=80°C	-0.35
Pulsed Drain Current	I _{DM}	-1.0	A
Continuous Source Current(Diode Conduction)	I _S	-0.3	A
Power Dissipation	P _D	TA=25°C	0.35
		TA=70°C	0.19
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C



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ELECTRICAL CHARACTERISTICS

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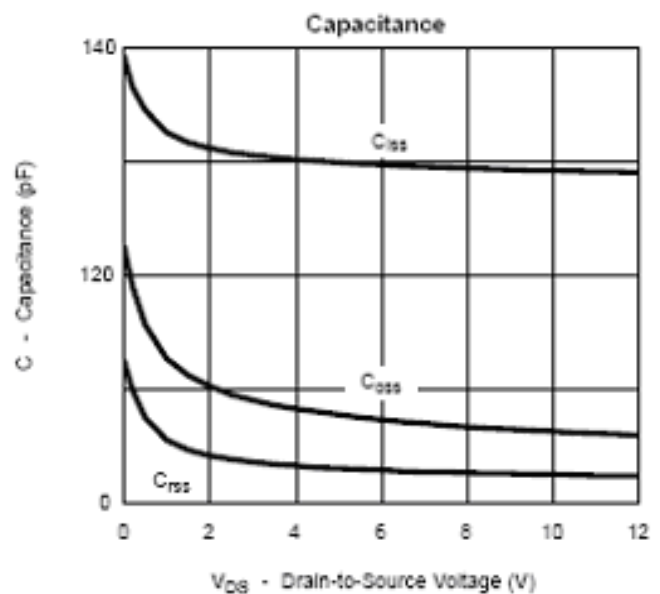
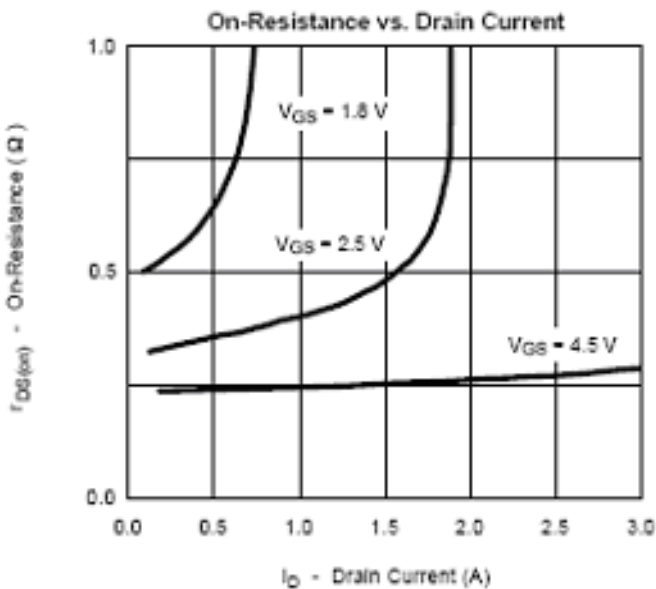
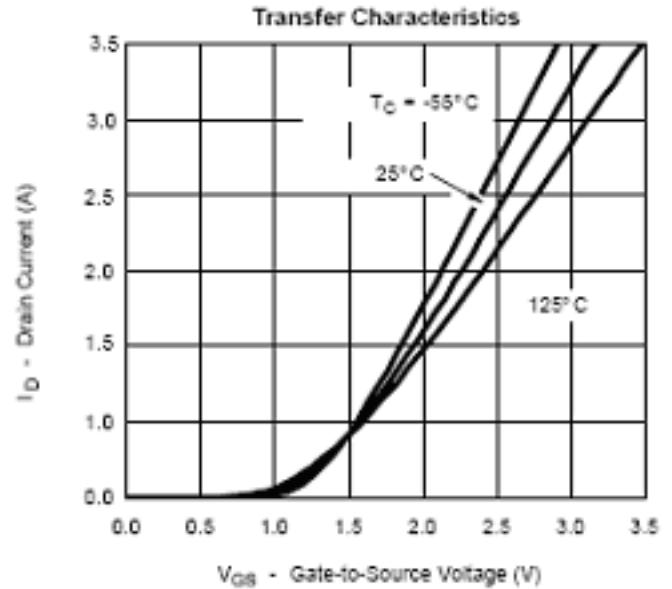
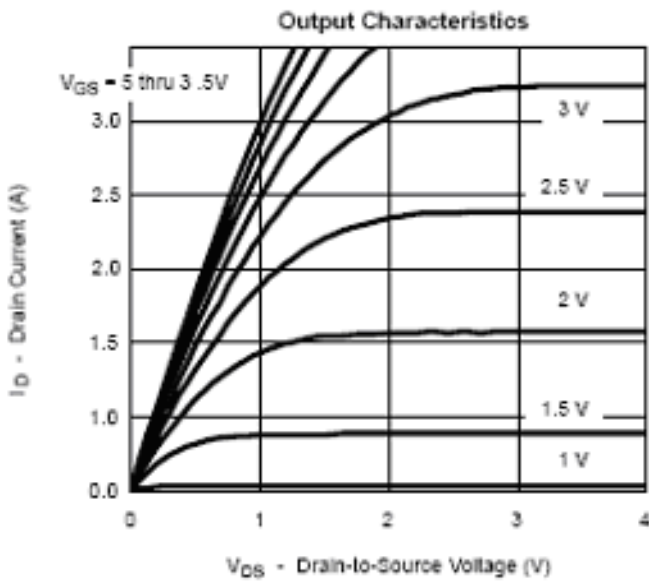
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.35		-1.0	V
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 30	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	μA
		$V_{DS}=-24V, V_{GS}=0V$ $T_J=55^\circ C$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS}\leq -4.5V, V_{GS}=-5V$	-0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-0.45A$		0.52	0.65	Ω
		$V_{GS}=-2.5V, I_D=-0.35A$		0.73	0.90	
		$V_{GS}=-1.8V, I_D=-0.25A$		1.10	1.50	
Forward Transconductance	g_{fs}	$V_{DS}=-10V, I_D=-0.25A$		0.4		S
Diode Forward Voltage	V_{SD}	$I_S=-0.15A, V_{GS}=0V$		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-0.6A$		1.5	2.0	nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.35		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=10\Omega, I_D=-0.4A$ $V_{GEN}=-4.5V, R_G=6\Omega$		5	10	ns
	t_r			15	25	
Turn-Off Time	$t_{d(off)}$			8	15	
	t_f			1.4	1.8	



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TYPICAL CHARACTERISTICS

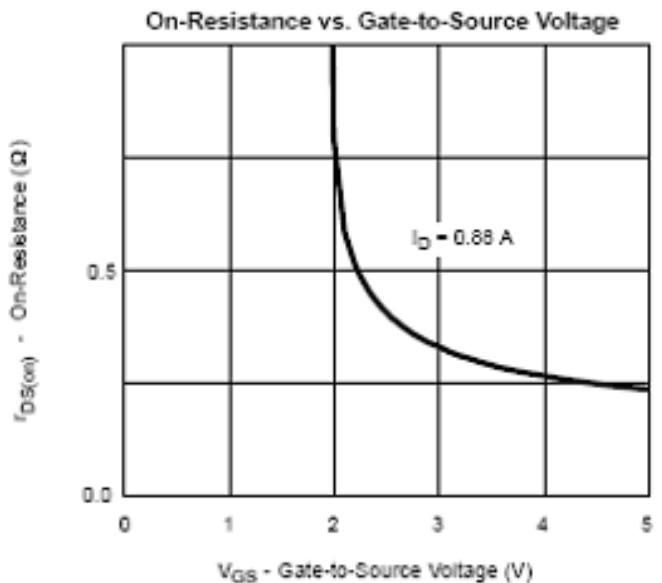
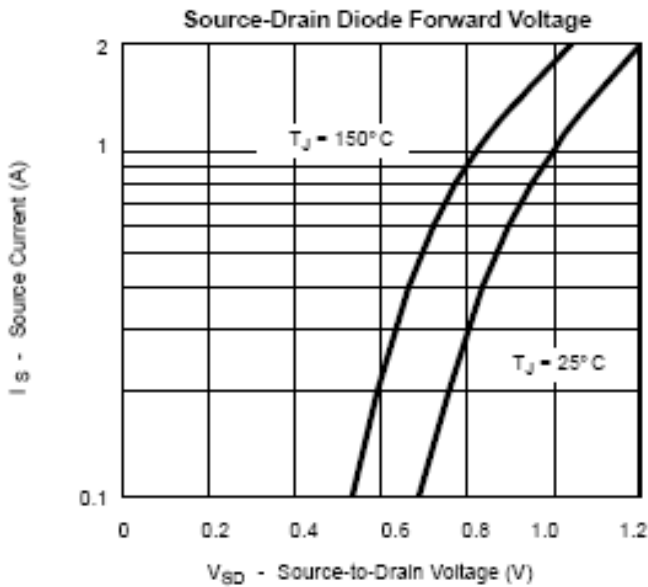
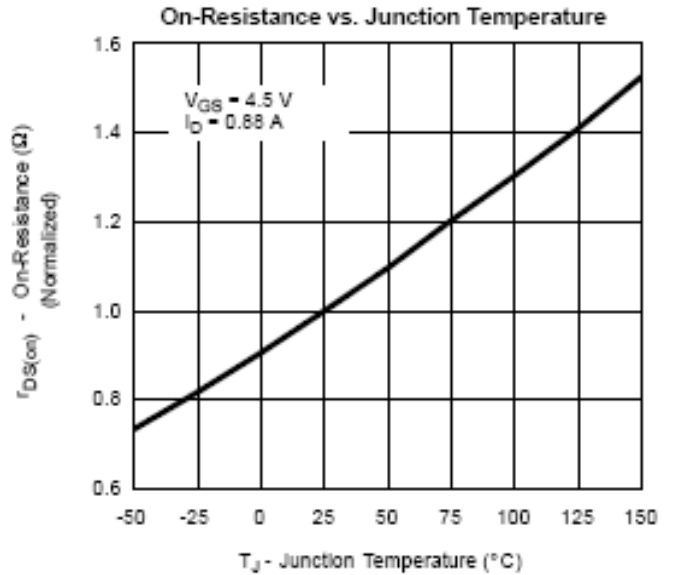
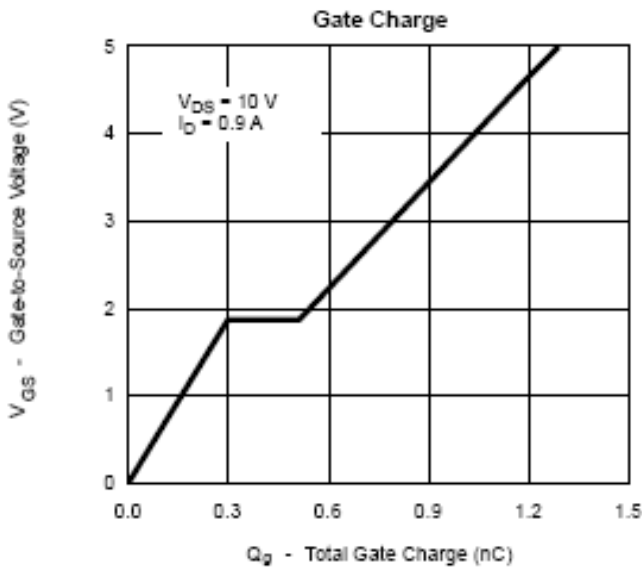




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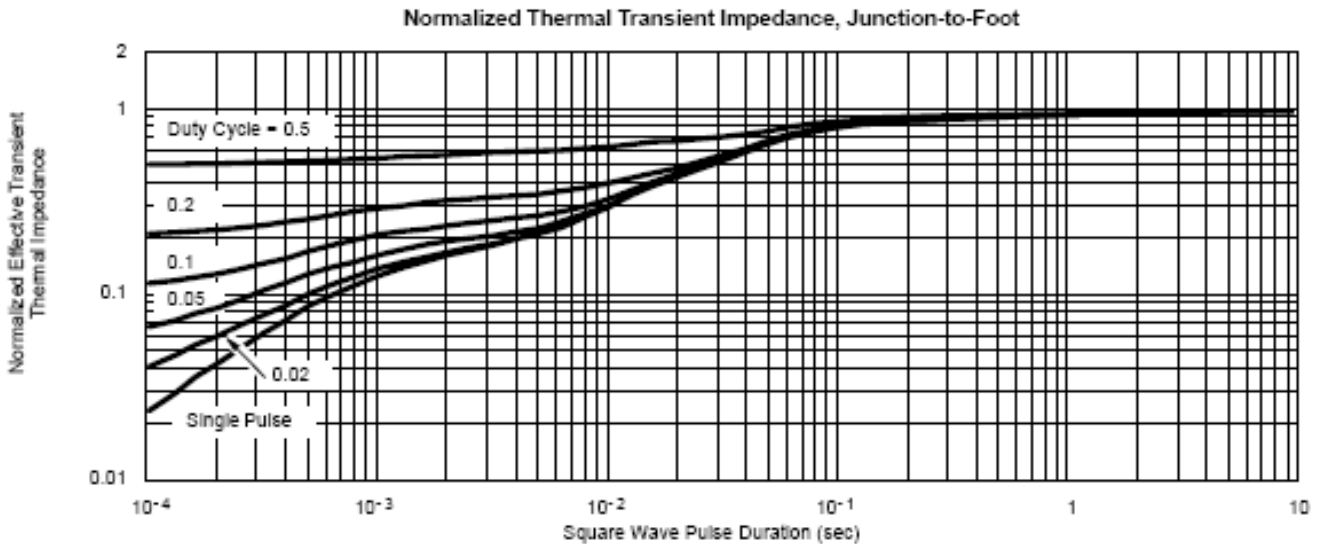
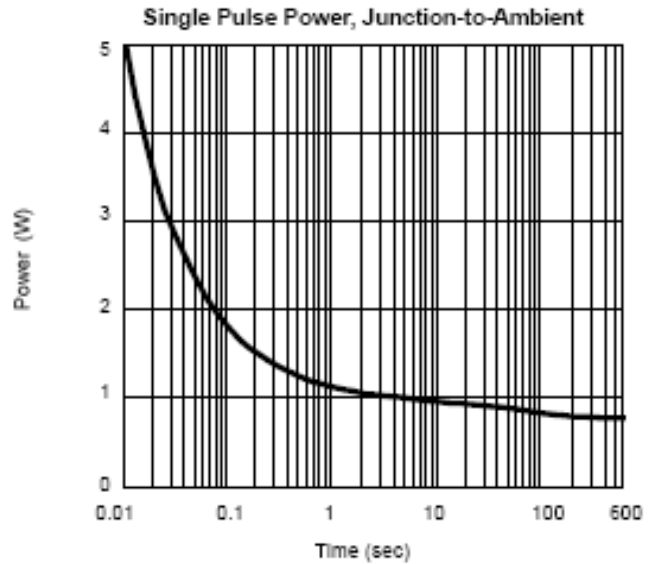
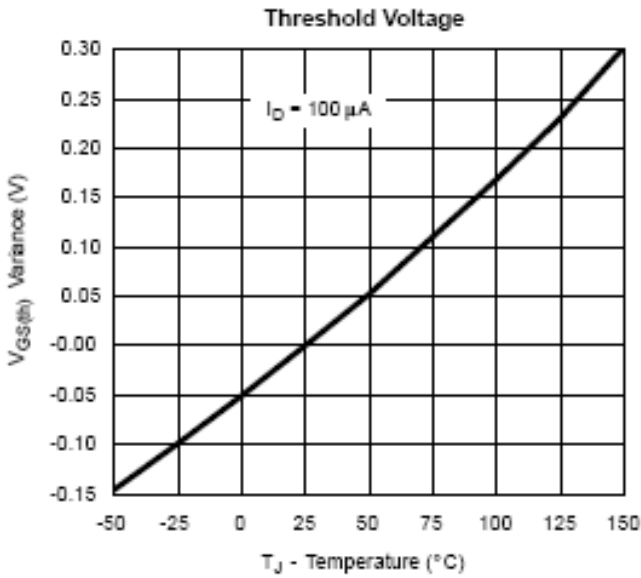




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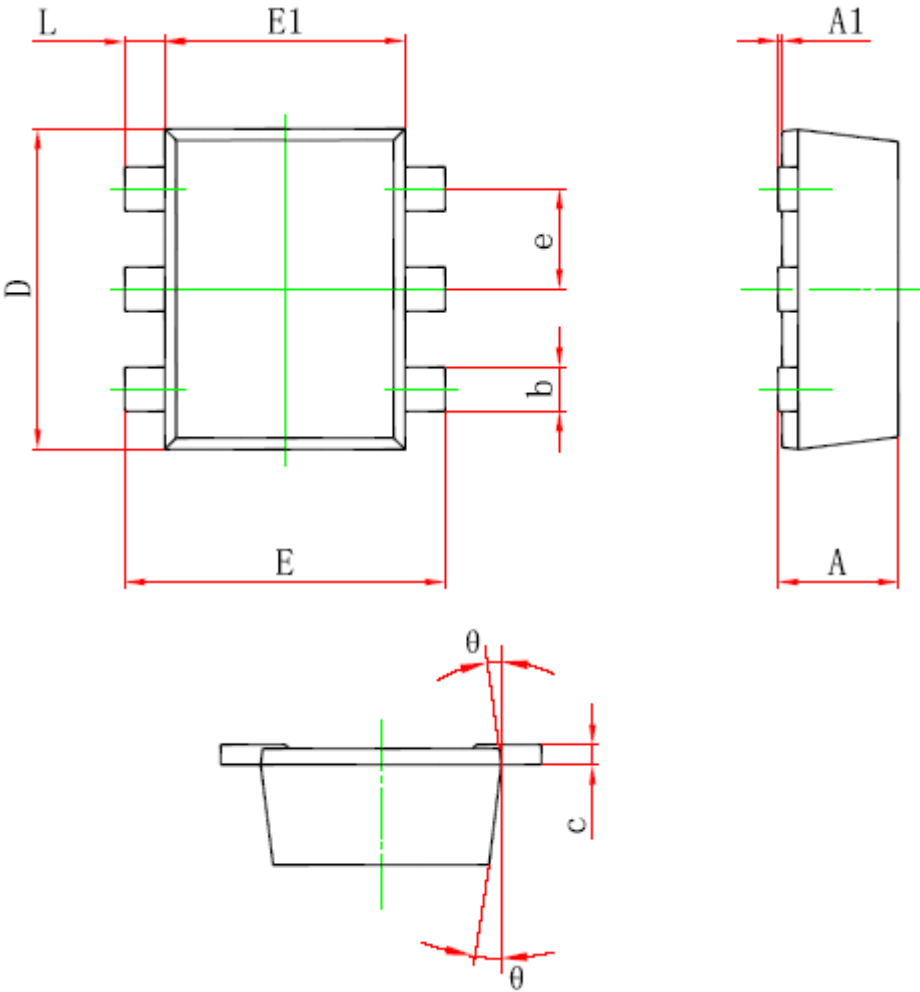




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SOT-563 PACKAGE OUTLINE



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
θ	7 °REF.		7 °REF.	



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